

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Not for submission under 37 CFR 1.99)

Application Number	10596327
Filing Date	2004-11-24
First Named Inventor	MARSH et al.
Art Unit	2828
Examiner Name	Not Yet Assigned
Attorney Docket Number	35832.000127

U.S.PATENTS

Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
/A.P./	1	6027989	A	2000-02-22	Poole et al.	
/A.P./	2	5071786	A	1991-12-10	Paoli	

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Receipt date: 11/17/2006		Application Number	10596327	10596327 - GAU: 2893
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Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.	T5
/A.P./	1	TAEK, Y. et al., "Effect of dielectric -semiconductor capping layer combination on the dielectric cap quantum well disordering of InGaAs/InGaAsP quantum well structure", Technical Digest CLEO / Pacific Rim '99, Pacific Rim Conference on Lasers and Electro Optics Cat. No. 99TH8464, Vol. 3, p. 3 (1999)	<input type="checkbox"/>
/A.P./	2	LIM, H. et al., "A novel fabrication technique for multiple-wavelength photonic-integrated devices in InGaAs-InGaAsP laser heterostructures", IEEE Photonics Technology Letters, 14:594-6 (May 2002)	<input type="checkbox"/>
/A.P./	3	LIU, X. et al., "Control of multiple bandgap shifts in InGaAs-AlInGaAs mutliple-quantum-well material using different thicknesses of PECVD SiO ₂ / protection layers", IEEE Photonics Technology Letters 12:1141-2 (2000)	<input type="checkbox"/>
/A.P./	4	OOI, B., et al., "Selective Quantum-Well intermixing in GaAs-AlGaAs Structures Using Impurity-Free Vacancy Diffusion", IEEE J. Q. Elect. 33:1784-1793 (1997)	<input type="checkbox"/>
/A.P./	5	AIMEZ, B. et al., "High precision metal masking for multiple wavelength laser diode fabrication using single step ion implantation induced quantum well intermixing," Proc. of the SPIE The International Society for Optical Engineering 4087:607-15 (2000)	<input type="checkbox"/>
/A.P./	6	COLDREN, L., "ECE Technical Report 03-02: 2002 Reprints of Professor Larry A. Coldren and Collaborators", Dept. of Electrical and Computer Engineering, University of California, Santa Barbara (2002)	<input type="checkbox"/>
/A.P./	7	COLDREN, L., "Publication List, Section 1B "Quantum-Well-Intermixing for Photonic ICs", http://www.ece.ucsb.edu/Faculty/Coldren/reprints/2002Reprint/2002ListofPubs.pdf , downloaded 6/9/2006 ed: Dept. of Electrical & Computer Engineering, University of California, Santa Barbara (2003)	<input type="checkbox"/>
/A.P./	8	Written Opinion of the ISA/EP in International Application No. PCT/GB2004/004944, mailed March 11, 2005.	<input type="checkbox"/>
/A.P./	9	UNITED KINGDOM PATENT OFFICE, Search Report in UK Patent Application Number GB0328808.1, May 25, 2004	<input type="checkbox"/>
/A.P./	10	KOCH, T. L. et al., "Tapered Waveguide InGaAs/InGaAsP Multiple-Quantum-Well Lasers", IEEE Photonics Technology Letters, 2:88-90 (February 1990)	<input type="checkbox"/>

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/A.P./	11	MOERMAN, I. et al., "A Review on Fabrication Technologies for the Monolithic Integration of Tapers with III-V Semiconductor Devices", IEEE Journal of Selected Topics in Quantum Electronics, 3:1308-1320 (December 1997)	<input type="checkbox"/>
/A.P./	12	BROEKAERT, T. et al., "AlAs Etch-Stop Layers for InGaAlAs/InP Heterostructure Devices and Circuits", IEEE Transactions on Electron Devices, Vol 39, No. 3, p. 333-336 (March 1992)	<input type="checkbox"/>

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Examiner Signature	/Allen Parker/	Date Considered	03/22/2010
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